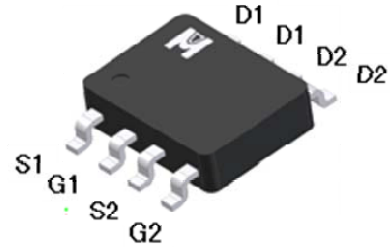
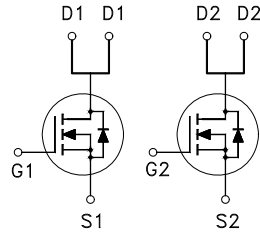


Dual N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	30V
R _{DS(on)} (MAX.)	21mΩ
I _D	7.5A



UIS, R_g 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A = 25 °C	I _D	7.5	A
	T _A = 100 °C		5.5	
Pulsed Drain Current ¹		I _{DM}	30	
Avalanche Current		I _{AS}	10	
Avalanche Energy	L = 0.1mH, I _D =7.5A, R _G =25Ω	E _{AS}	2.8	mJ
Repetitive Avalanche Energy ²	L = 0.05mH	E _{AR}	1.4	
Power Dissipation	T _A = 25 °C	P _D	2	W
	T _A = 100 °C		0.8	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

100% UIS testing in condition of V_D=15V, L=0.1mH, V_G=10V, I_L=7.5A, Rated V_{DSS}=30V N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		25	°C / W
Junction-to-Ambient ³	R _{θJA}		62.5	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³62.5°C / W when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^\circ\text{C}$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	7.5			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 7.5A$		18	21	m Ω
		$V_{GS} = 4.5V, I_D = 5.5A$		34	42	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 7.5A$		16		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		520		pF
Output Capacitance	C_{oss}			88		
Reverse Transfer Capacitance	C_{rss}			62		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		2.0		Ω
Total Gate Charge ^{1,2}	$Q_g(V_{GS}=10V)$	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 7.5A$		11.5		nC
	$Q_g(V_{GS}=5V)$			5		
Gate-Source Charge ^{1,2}	Q_{gs}			1.6		
Gate-Drain Charge ^{1,2}	Q_{gd}			2.8		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$		$V_{DS} = 15V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		9	
Rise Time ^{1,2}	t_r			12		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			30		
Fall Time ^{1,2}	t_f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$)						
Continuous Current	I_S				2.3	A
Pulsed Current ³	I_{SM}				9.2	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, di_F/dt = 100A / \mu S$		50		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			30		A
Reverse Recovery Charge	Q_{rr}			2		nC

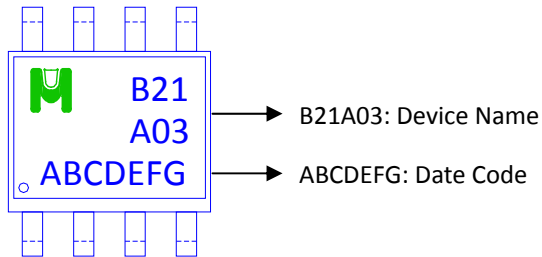
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

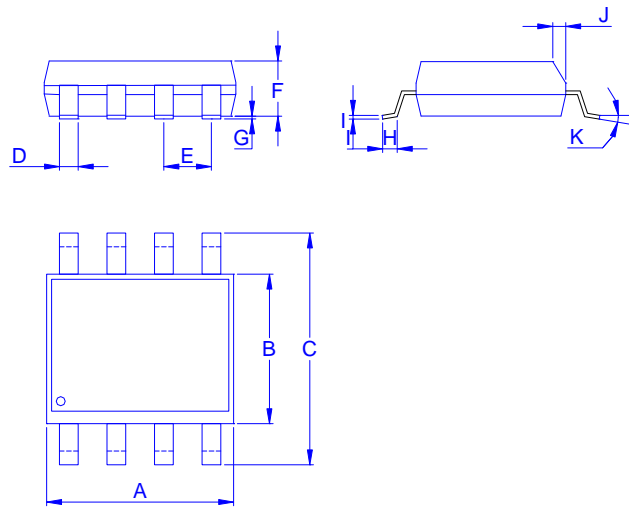
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMB21A03G for SOP-8



Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K
in.	4.70	3.70	5.80	0.33		1.20	0.08	0.40	0.19	0.25	0°
Typ.					1.27						
Max.	5.10	4.10	6.20	0.51		1.62	0.28	0.83	0.26	0.50	8°

